

Product Summary

BV_{DSS}	R_{DSON} Max	I_D Max T_C = +25°C
-30V	20mΩ @ V _{GS} = -10V	-30A
	29mΩ @ V _{GS} = -5V	-30A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DSON}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

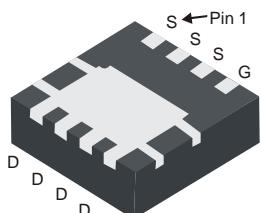
Features and Benefits

- Low R_{DSON} – ensures on state losses are minimized.
- Small form factor thermally efficient package enables higher density end products.
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product.
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

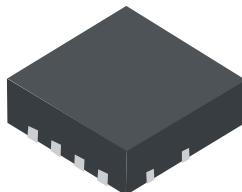
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208^③
- Weight: 0.03 grams (Approximate)

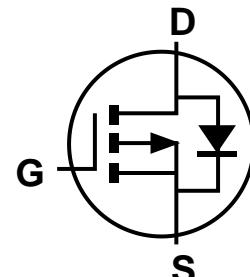
PowerDI3333-8



Bottom View



Top View



Equivalent Circuit

Ordering Information (Note 4)

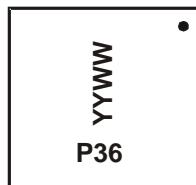
Part Number	Case	Packaging
DMP3036SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMP3036SFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

PowerDI3333-8



P36 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 17 = 2017)
 WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	-30	V	
Gate-Source Voltage	V_{GSS}	± 25	V	
Continuous Drain Current (Note 6) $V_{GS} = -10\text{V}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-8.7 -7.0	A
Continuous Drain Current (Note 7) $V_{GS} = -10\text{V}$	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	I_D	-30 -25	A
Continuous Drain Current (Note 6) $V_{GS} = -5\text{V}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-7.2 -5.8	A
Continuous Drain Current (Note 7) $V_{GS} = -5\text{V}$	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	I_D	-30 -24	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	-80	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	-3.6	A	
Avalanche Current (Note 7) $L=0.3\text{mH}$	I_{AS}	-17.5	A	
Avalanche Energy (Note 7) $L=0.3\text{mH}$	E_{AS}	64	mJ	

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	137	$^\circ\text{C}/\text{W}$
		65	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	55	$^\circ\text{C}/\text{W}$
		26	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	3.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1.0	μA	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	13	20	$\text{m}\Omega$	$V_{GS} = -10\text{V}, I_D = -8\text{A}$
		-	18.4	29		$V_{GS} = -5\text{V}, I_D = -5\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.7	-1.2	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	1931	-	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	226	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	168	-	pF	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Gate Resistance	R_g	-	10.9	-	Ω	
Total Gate Charge $V_{GS} = -5\text{V}$	Q_g	-	8.8	-	nC	$V_{DS} = -15\text{V}, I_D = -10\text{A}$
Total Gate Charge $V_{GS} = -10\text{V}$	Q_g	-	16.5	-	nC	
Gate-Source Charge	Q_{gs}	-	2.6	-	nC	$V_{DS} = -10\text{V}, V_{DD} = -15\text{V}, R_{GEN} = 3\Omega, I_D = -10\text{A}$
Gate-Drain Charge	Q_{gd}	-	3.6	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	8.2	-	ns	$V_{GS} = -10\text{V}, V_{DD} = -15\text{V}, R_{GEN} = 3\Omega, I_D = -10\text{A}$
Turn-On Rise Time	t_R	-	14	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	65	-	ns	$I_F = -8\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Turn-Off Fall Time	t_F	-	31.6	-	ns	
Reverse Recovery Time	t_{RR}	-	9.3	-	ns	$I_F = -8\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	-	12.2	-	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

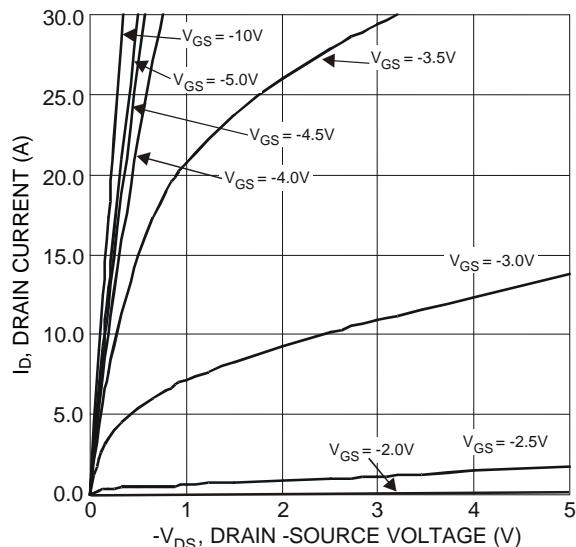


Figure 1 Typical Output Characteristics

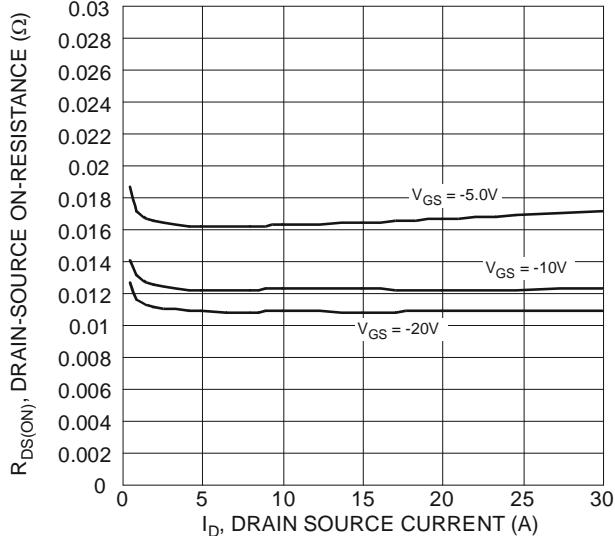


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

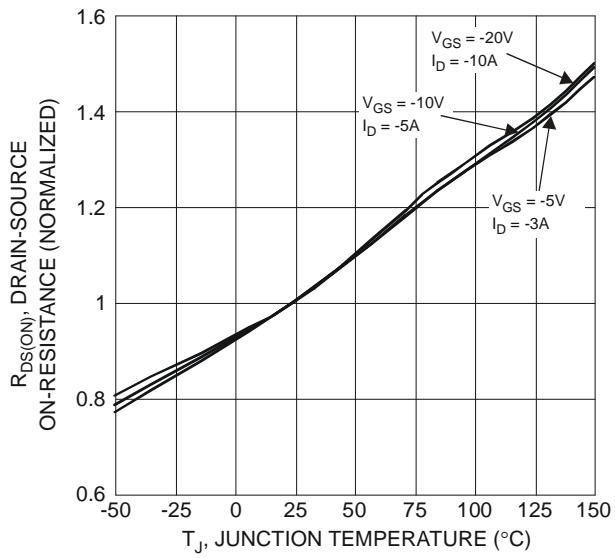


Figure 5 On-Resistance Variation with Temperature

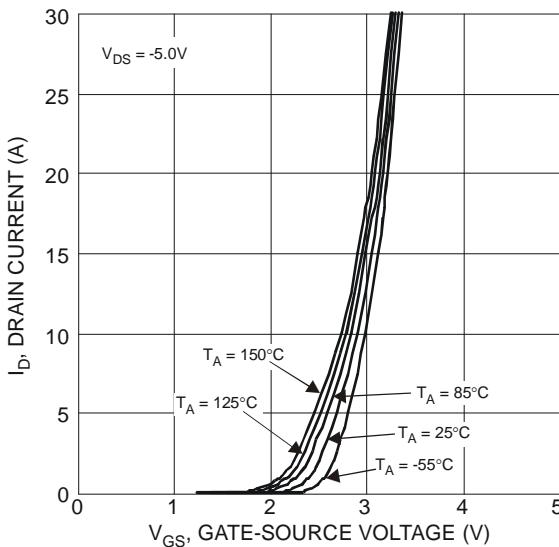


Figure 2 Typical Transfer Characteristics

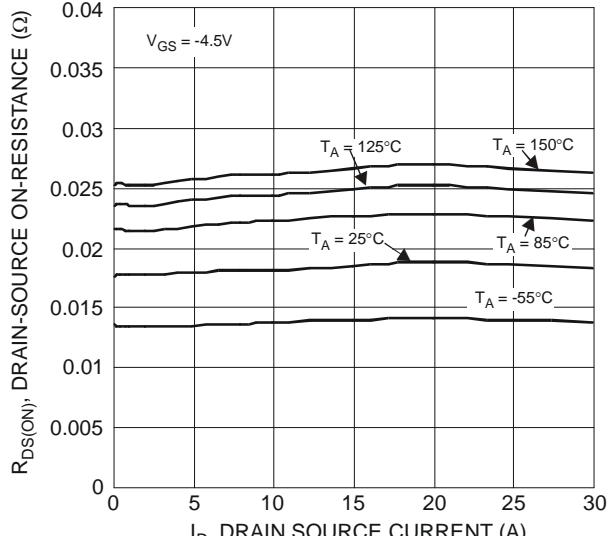


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

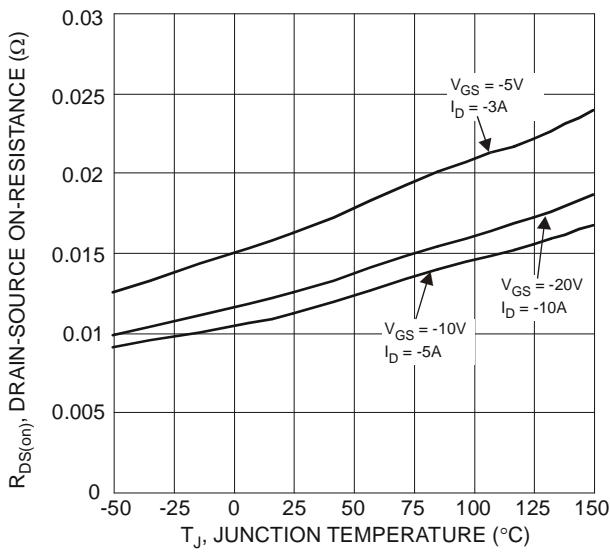


Figure 6 On-Resistance Variation with Temperature

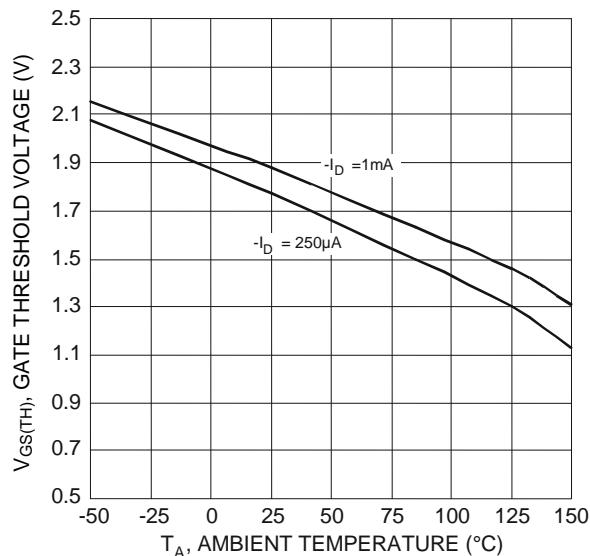


Figure 7 Gate Threshold Variation vs. Ambient Temperature

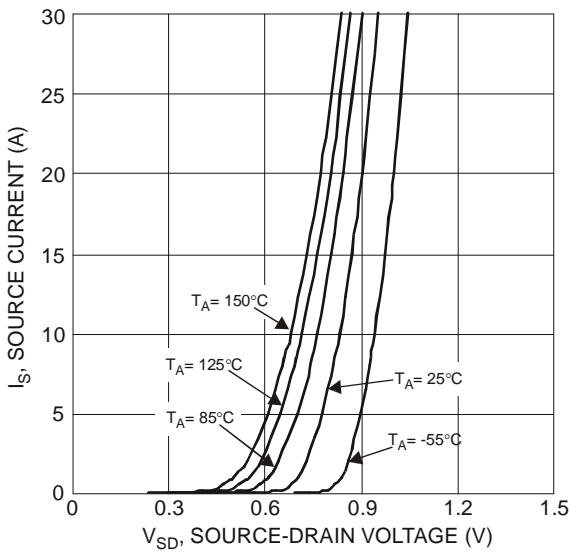


Figure 8 Diode Forward Voltage vs. Current

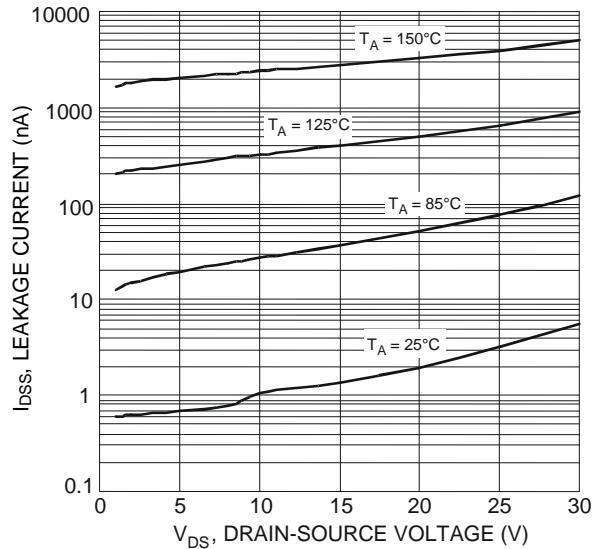


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

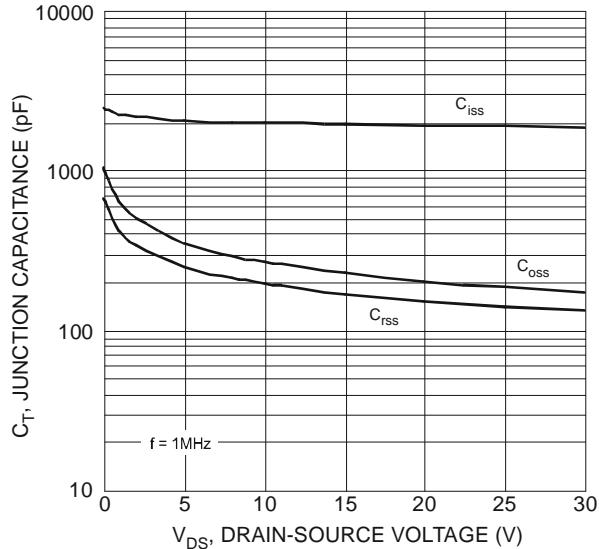


Figure 10 Typical Junction Capacitance

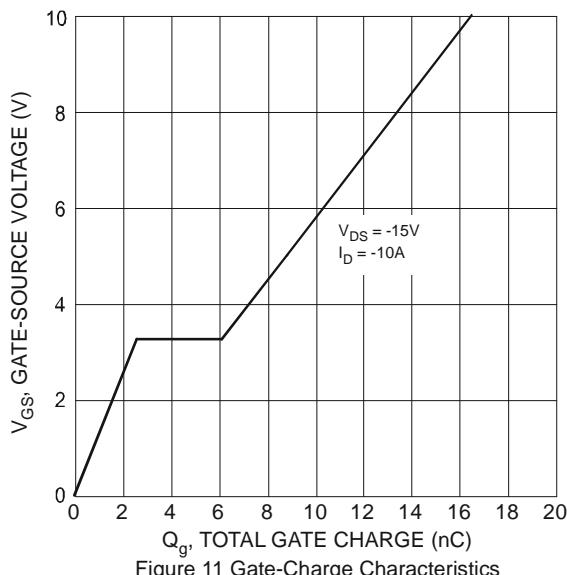


Figure 11 Gate-Charge Characteristics

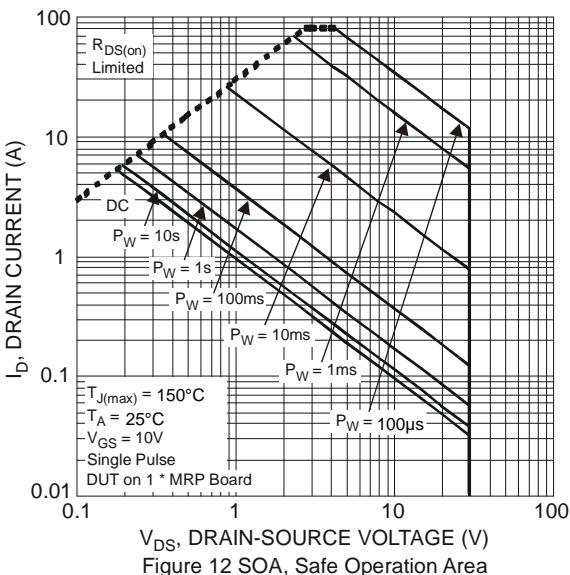


Figure 12 SOA, Safe Operation Area

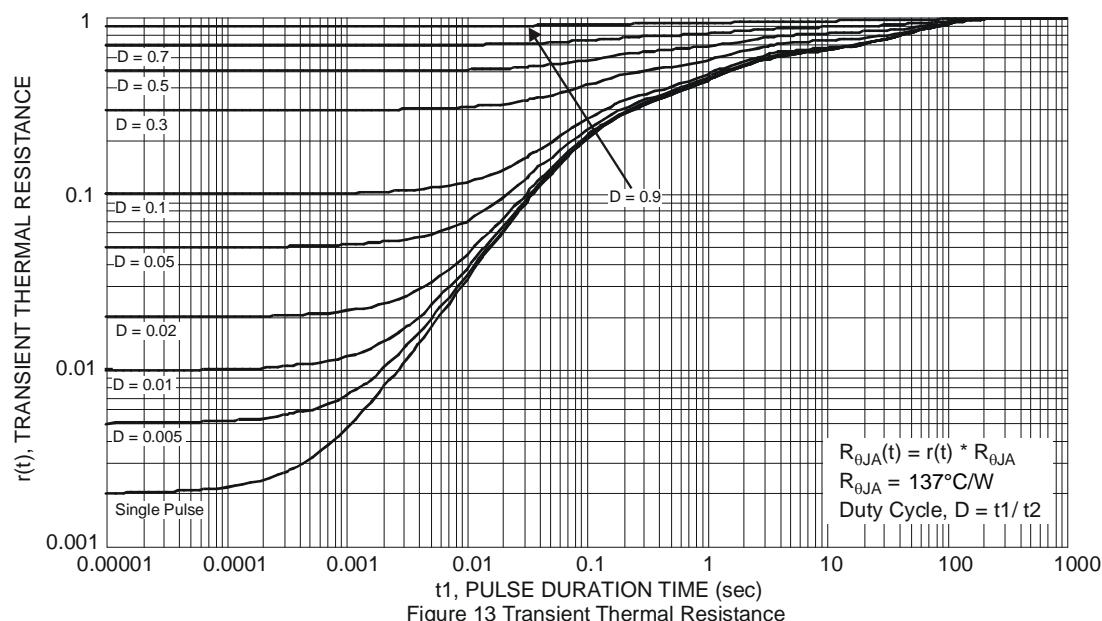
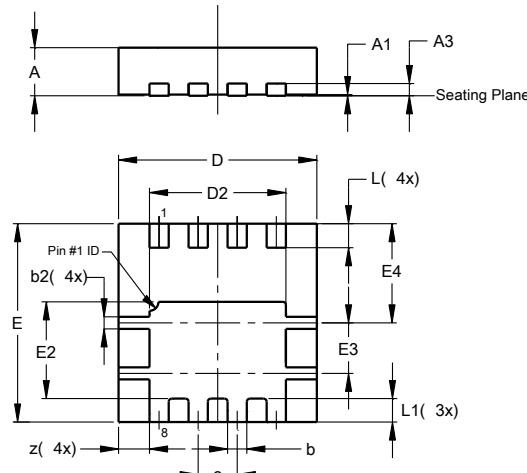


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



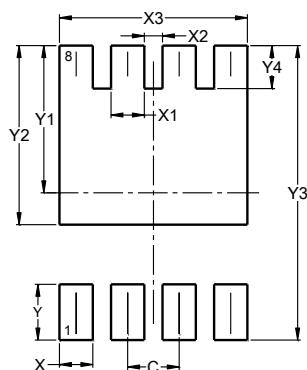
PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	—	—	0.65
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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